INTERNATIONAL RECTIFIER

A-29-07

SERIES DP

Integrated Circuit Solid-State Relay

> 1 Amp 5-280V AC

GENERAL DESCRIPTION

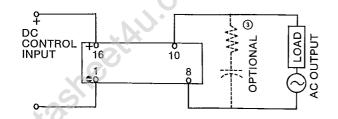
The Crydom ChipSwitch uses the exclusive International Rectifier S³X power integrated circuit technology to form a fully functioning solid-state relay. The S³X technology combines MOS and bipolar processes, derived from IR's HEXFET® power MOSFET designs, to eliminate the need for both discrete components and hybrid circuits. The basic ChipSwitch consists simply of two identical power integrated circuits connected in inverse parallel (analogous to back-to-back SCRs) for AC control plus an isolated light emitting diode (LED) for actuation. Voltage controlled models with an internal resistor to limit the control current are also available.

Extreme reliability is achieved by the reduction of component count from approximately 20 discrete components in a conventional SSR to 3 basic components in the ChipSwitch. The power integrated circuits are fabricated in IR's advanced MOSFET fabrication plant which achieves standards of cleanliness, precision, and consistency unprecedented in the manufacture of power semiconductors.

The <u>ChipSwitch</u> is a normally open SSR of 1.0 ampere rating with precise zero voltage turn-on and zero current turn-off. EMI emission conforming to the most severe FCC and VDE requirements.

The devices are ideally suited for interfacing microprocessors to AC loads such as small motors, lamps, solenoids, valves, and high power motor starters. The economy of the ChipSwitch allows the in-house manufacturer to replace assemblages of triacs, triac drivers and associated components with a highly reliable, miniature, standard SSR.

WIRING DIAGRAM



S³X Power IC Chips G 30 Amps Surge G

3750V RMS Isolation □

Zero Voltage Turn-On 🗆

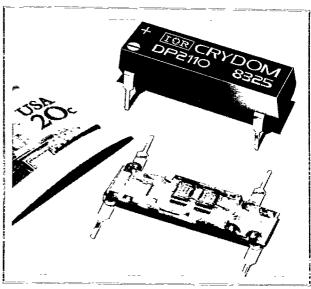
EMI Meets FCC/VDE Limits

600V/ μ sec dv/dt \Box

10 Microamps Leakage

TO-116 Pinout

<u>ChipSwitch</u>



Part Identification

Part No.	Operating Voltage	DC Input Turn-On	
DP1110 DP1210 DP1610	5 to 140VAC	5 mA 10 mA 3.5 V	
DP2110 DP2210 DP2610	5 to 280VAC	5 mA 10 mA 3.5 V	

CRYDOM CO

2542537 0000498 8 **CR**Y)

GENERAL CHARACTE	RISTICS		
Dielectric Strength — I	nput/Output	3750	V (RMS
Insulation Resistance (⊚ 500VDC — Input/Output	109	Ohms
Max Capacitance — In	put/Output	1.0	pf
Ambient Temperature	Operating	-30 to 80	°C
Range	Storage	-40 to 100	°C

ELECTRICAL SPECIFICATIONS (-30° C \leqslant TA \leqslant 80° C unless otherwise specified)

INPUT CHARACTERISTICS	DP1110	DP1210	DP1610	DP2110	DP2210	DP2610	Units
Control Current Range (see Fig. 3)	5-20	10-20	N/A	5-20	10-20	N/A	mA (DC)
Control Voltage Range (see Fig. 4)	N	/A	3.5-7	N	/A 	3.5-7	V (DC)
Max Reverse Voltage	7.0					V (DC)	
Max Turn-On Voltage	N	/A	3.5	N	/A	3.5	V (DC)
Min Turn-Off Voltage	N	/A	0.8	N	//A	0.8	V (DC)
Mín Input Impedance	N	/A	270	N/A 2		270	Ohms
Max Turn-On Current	5.0	10	N/A	5.0	10	N/A	mA (DC)
Min Turn-Off Current	0.5		N/A	N/A 0.5		N/A	mA (DC)
Max Turn-On Time (60 Hz)	8.3				mSec		
Max Turn-Off Time (60 Hz)	8.3			mSec			

OUTPUT CHARACTERISTICS

Operating Voltage Range 47-63 Hz	5-140	5-280	V (RMS)
Transient Overvoltage (Non-Repetitive)	300	450	V (peak)
Min Off-State dv/dt (static) ①③ @ Max Rated Voltage (25°C)		600	V/μs
Max Load Current (see Fig. 1) ②		A (RMS)	
Min Load Current		mA (RMS)	
Max Surge Current (Non-Rep.) 20 ms (see Fig. 2)		A (peak)	
Max Over Current (Non-Rep.) 1 sec		A (peak)	
Max On-State Voltage Drop @ Rated Current		V (peak)	
Max 1 ² T for Fusing (.01 sec)		A²sec	
Max Zero Voltage Turn-On		V (peak)	
Max Peak Repetitive Turn-On Voltage		V (peak)	
Max Off-State Leakage Current @ Rated Voltage		10	A (RMS)

GENERAL NOTES ① Off-state dv/dt test method per EIA/NARM standard RS-443 with V_p equal to the instantaneous peak of the maximum operating voltage.
② Parameters are met at 0.5 power factor or greater.

① The application of an RC snubber (see front cover wiring diagram) is good practice when operating inductive loads at high ambient temper-atures and under heavy load conditions. Typical values are 0.03 mfd plus 10 ohms. Consult factory for application aid.

ChipSwitch™ PERFORMANCE CHARACTERISTICS CURVES

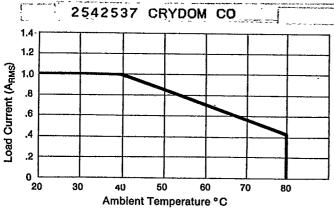


Figure 1. Derating Curve

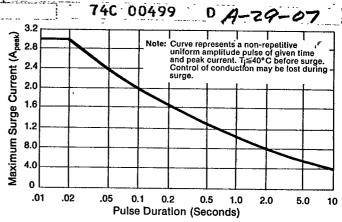


Figure 2. Maximum Allowable Surge

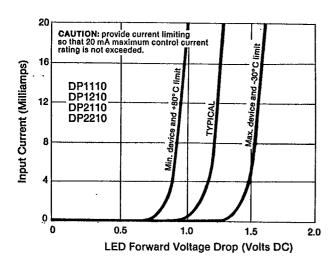


Figure 3. Input Characteristics (Current Controlled)

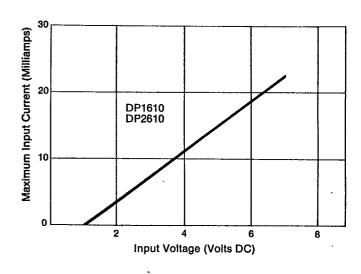


Figure 4. Input Characteristics (Voltage Controlled)

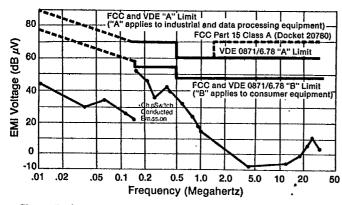


Figure 5. Conducted Electromagnetic Interference

